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IN THE CLAIMS

Claim 1 (Canceled)

B, 2. (Currently Amended) An information storage medium which ~~has~~ comprises a substrate and, stacked thereon in the following successive order, at least a protective layer, a first interfacial layer which is comprised of an oxide or a nitride, a recording layer, and at least two layers containing 60 atomic % or more of at least one metal element ~~at the more back side than the recording film when seen from the light incident side, wherein one of the said at least two layers containing contains 60 atomic % or more of at least one metal element having an atomic number of not less than 22 and not more than 47, and having has a film thickness of 30 nm or more.~~

3. (Currently Amended) The information storage medium according to claim 2 wherein ~~the layer containing 60 atomic % or more of metal contain~~ said one of the at least two layers contains 60 atomic % or more of at least one metal element having an atomic number of not less than 22 and not more than 28 and have a film thickness of 30 nm or more.

4. (Currently Amended) The information storage medium according to claim 2, ~~which have~~ having three of said above

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~~mentioned~~ layers containing 60 atomic % or more of at least one metal element.

5. (Currently Amended) The information storage medium according to claim 2, wherein the at least one metal element having an atomic number of not less than 22 and not more than 47 is at least one of Ti and Cr.

6. (Currently Amended) The information storage medium according to claim 2 wherein, among the at least two layers each ~~comprising~~ containing 60 atomic % or more of at least one metal element ~~as the main component~~, the layer nearest to the light incident side comprises Cr or Mo as the main component.

B,
cont.

7. (Currently Amended) The information storage medium according to claim 2 wherein the layer ~~comprising metal as the main component~~ which contains 60 atomic % of at least one metal element having an atomic number of not less than 22 and not more than 47 and has a film thickness of 30 nm or more ~~is present on the more front side, which seen from~~ nearer the light incident side, than the other layer(s) comprising metal as the main component containing 60 atomic % or more of at least one metal element.

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8. (Currently Amended) The information storage medium according to claim 2 wherein the layer ~~composing metal as the main component~~ which contains 60 atomic % or more of at least one metal element having an atomic number of not less than 22 and not more than 47 and has a film thickness of 30 nm or more is ~~present on the more back side, when seen from less near the light incident side,~~ than the other layer(s) ~~comprising metal as the main component~~ containing 60 atomic % or more of at least one metal element.

B,
cont.

9. (Currently Amended) The information storage medium according to claim 8, wherein the layer(s) ~~comprising metal as the main component~~ containing 60 atomic % or more of at least one metal element other than the ~~above-mentioned layer comprising metal as the main component~~ which contains 60 atomic % or more of having at least one metal element having an atomic number of not less than 22 and not more than 47, ~~and has a film thickness of 30 nm or more~~ contain(s) 70 atomic % or more of Al or Ag.

10. (Currently Amended) The information storage medium according to claim 2 wherein ~~the~~ a layer between the recording layer and the at least two metal layers and recording film containing 60 atomic % or more at least one metal element is at least one dielectric material layer, and the whole

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thickness of the at least one dielectric material layer is not less than 10 nm and not more than 50 nm.

11. (Currently Amended) The information storage medium according to claim 2, wherein the layer containing 60 atomic % or more of at least one metal element having an atomic number of not less than 22 and not more than 47 has a film thickness of not less than 50 nm and not more than 150 nm.

Claim 12-15 (Canceled)

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cont.
16. (Currently Amended) The information storage medium according to claim 2, wherein the recording film layer effects recording by phase change.

17. (Currently Amended) The information storage medium according to claim 2, wherein the substrate of the medium has a recording track pitch of not less than 0.3 μm and not more than 0.7 μm and has pit trains which represent at least address information, ~~etc.~~ at positions shifted from the track center.

18. (Currently Amended) The information storage medium according to claim 8 wherein the ~~other layer(s) comprising metal as the main component~~ containing 60 atomic % or more of at least one metal element, other than the layer having at

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least one metal element having an atomic number of not less than 22 and not more than 47, comprise(s) Ag as the main component, and the number of stacked layers of the recording stacked film is 6.

19. (Currently Amended) ~~An~~ The information storage medium ~~which effects writing and reading by laser light which has a~~ according to claim 2, wherein said layer containing 60 atomic % or more of at least one metal element having an atomic number of not less than 22 and not more than 47, said film being a film is formed at an Ar flow rate of 120 sccm or more.

B1
CONT.
20. (Currently Amended) A method of manufacturing an information storage medium which effects writing and reading by laser light, which method comprises forming a layer containing 60 atomic % or more of at least one metal element having an atomic number of not less than 22 and not more than 47 at an Ar flow rate of 120 sccm or more.

21. (Currently Amended) An information storage medium which ~~has~~ comprises a substrate and, stacked thereon in the following successive order, at least a protective layer, a first interfacial layer, a recording layer, and at least one layer containing 60 atomic % or more of at least one metal

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element having an atomic number of not less than 22 and not more than 47 and having a film thickness of 30 nm or more.

B₁
Cont.

22. (Original) The information storage medium according to claim 21 wherein the above-mentioned layer containing 60 atomic % or more of at least one metal element having an atomic number of not less than 22 and not more than 47 is a layer of Ti-Cr or V-Cr alloy which contains not less than 30 atomic % and not more than 85 atomic % of Cr, and not less than 15 atomic % and not more than 70 atomic % of Ti or V.

23. (New) The information storage medium according to claim 2, wherein said one of the at least two layers containing 60 atomic % or more of at least one metal element having an atomic number of not less than 22 and not more than 47 and having a film thickness of 30 nm or more, has a pillar-like structure continuing from the lower face to the upper face of the layer in at least 80% of a section of the layer.

B₂

24. (New) The information storage medium according to claim 2, further comprising a second interfacial layer between said recording layer and said at least two layers each containing 60 atomic % or more of at least one metal element, wherein said second interfacial layer includes an oxide or a nitride.

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B2
cont. 25. (New) The information storage medium according to claim 2, wherein said first interfacial layer includes an oxide or a nitride of at least one element selected from the group comprising of Cr, Ge, Si, Al, Ta, Zr, B, Hf, and Ti.
